

Supplementary Information

High-throughput Screening of Plastic Deformable Inorganic Semiconductors

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Table S1. Information on all of the 612 kinds of materials. (TableS1.xlsx)

Table S2. Calculated cleavage energy E_c , slipping energy E_s , in-plane modulus E_{in} along the slipping direction, and the deformability factor Ξ for selected materials PbI_2 and CuInP_2S_6 .

Materials	E_c (eV/atom)	E_s (eV/atom)	E_{in} (GPa)	Factor Ξ (1/GPa)	Bandgap (eV)
PbI_2	0.067	0.066	18.2	0.056	2.5
CuInP_2S_6	0.052	0.02	93.63	0.026	2.2

Movie S1. A movie showing the plastic bending process of the single crystalline PbI_2 .

The movie is played at original speed. (MovieS1_PbI2.mp4)

Movie S2. A movie showing the plastic bending process of the single crystalline CuInP_2S_6 . The movie is played at original speed. (MovieS2_CuInP2S6.mp4)